

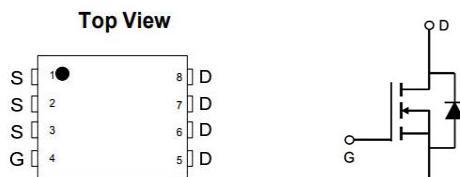
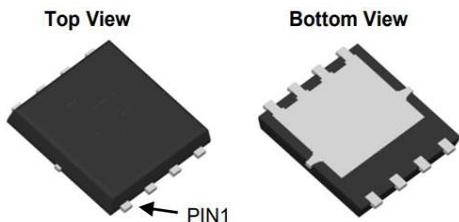
30V /85A Single N Power MOSFET
General Description

30V /85A Single N Power MOSFET

Very low on-resistance RDS(on) @ VGS=4.5 V

Pb-free lead plating; RoHS compliant

V_{DS}	30	V
R_{DS(on),TYP@VGS=10V}	2.5	mΩ
R_{DS(on),TYP@VGS=4.5}	4.0	mΩ
I_D	85	A



Part ID	Package Type	Marking	Tape and reel infomation
SM6358D1RL	DFN5x6	6358	3000


 100% UIS Tested
100% RG Tested

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V _{DS}	30	V
Gate-Source Voltage	V _{GS}	20	±V
Continuous Drain Current A TA=25°C	I _D	85.0	A
TA=70°C	I _D	67*	
Pulsed Drain Current B	I _{DM}	136.0	
Avalanche Current G	I _{AR}	27.2	
Repetitive avalanche energy L=0.1mH G	E _{AR}	62.6	mJ
Power Dissipation A TA=25°C	P _D	48	W
TA=70°C	P _D	19*	
Junction and Storage Temperature Range	T _J , T _{STG}	-55 to 150	°C

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient A	R _{θJA}	9	13	°C/W
Maximum Junction-to-Ambient A Steady State		18	21	°C/W
Maximum Junction-to-Lead c Steady State	R _{θJL}	5	8	°C/W

STATIC PARAMETERS

Symbol	Parameter	Conditions	Min	Typ	Max	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D = -250\mu A, V_{GS} = 0V$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$			1	uA
					5	
I_{GSS}	Gate-Body leakage current	$V_{DS} = 0V, V_{GS} = \pm 20V$			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.1	1.7	2.2	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=20A$		2.5	3.6	$m\Omega$
		$V_{GS}=4.5V, I_D=20A$		4.0	5.1	
g_{FS}	Forward Transconductance	$V_{DS}=5V, I_D=20A$		97		S
V_{SD}	Diode Forward Voltage	$I_S=1A, V_{GS}=212V$		0.72	1	V
I_S	Maximum Body-Diode Continuous Current				85	A

DYNAMIC PARAMETERS

Symbol	Parameter	Conditions	Min	Typ	Max	Units
C_{iss}	Input Capacitance	$V_{GS}=0V, V_{DS}=15V, f=1MHz$		2200	2684	pF
C_{oss}	Output Capacitance			1000	1230	pF
C_{rss}	Reverse Transfer Capacitance			100	119	pF
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, f=1MHz$			2.35	Ω

SWITCHING PARAMETERS

Symbol	Parameter	Conditions	Min	Typ	Max	Units
$Q_g(10V)$	Total Gate Charge	$V_{GS}=10V, V_{DS}=15V, I_D=20A$		15		nC
$Q_g 4.5V$	Total Gate Charge			7.5		
Q_{gs}	Gate Source Charge			3.29		
Q_{gd}	Gate Drain Charge			4.7		
$t_{D(on)}$	Turn-On Delay Time	$V_{GS}=10V, V_{DS}=15V, RL=0.75\Omega, R_{GEN}=3\Omega$		8.5		ns
t_r	Turn-On Rise Time			6.8		
$t_{D(off)}$	Turn-Off Delay Time			23.8		
t_f	Turn-Off Fall Time			7.65		
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-8A, dI/dt=500A/\mu s$		17		ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=18A, dI/dt=500A/\mu s$		42		nC

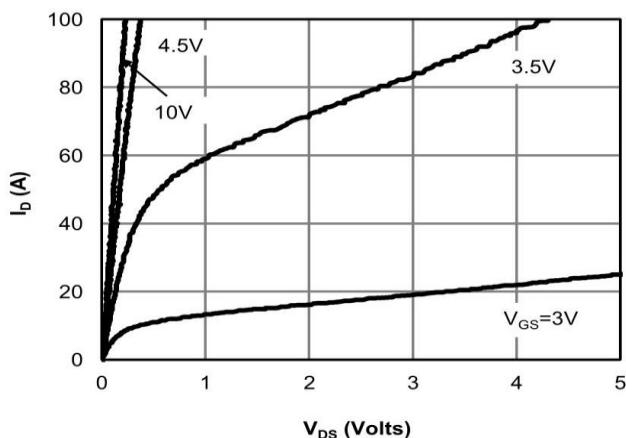
TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS


Figure 1: On-Region Characteristics (Note E)

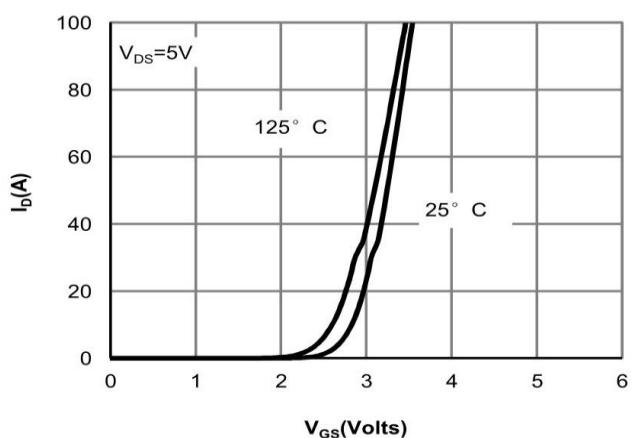


Figure 2: Transfer Characteristics (Note E)

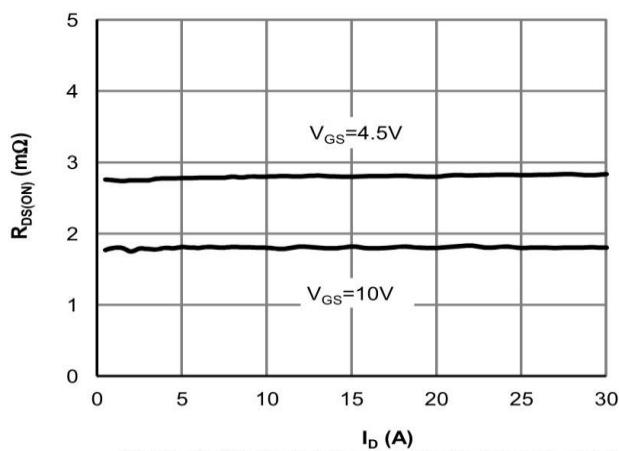


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

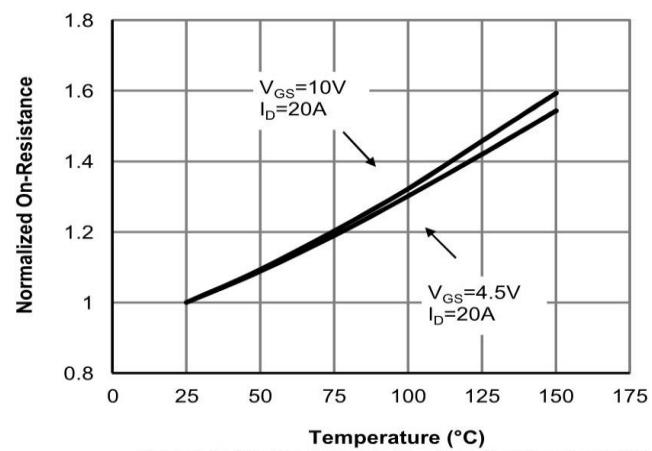


Figure 4: On-Resistance vs. Junction Temperature (Note E)

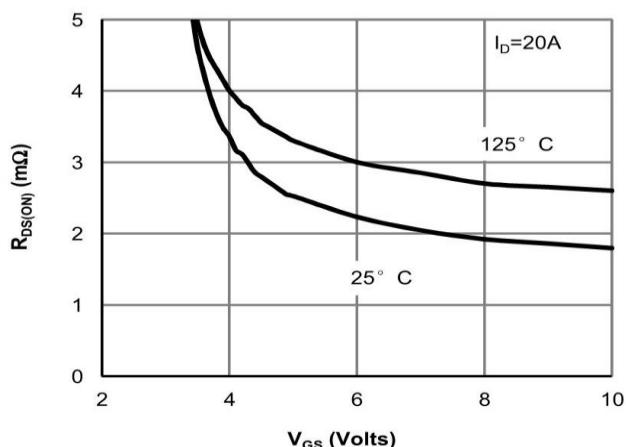


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

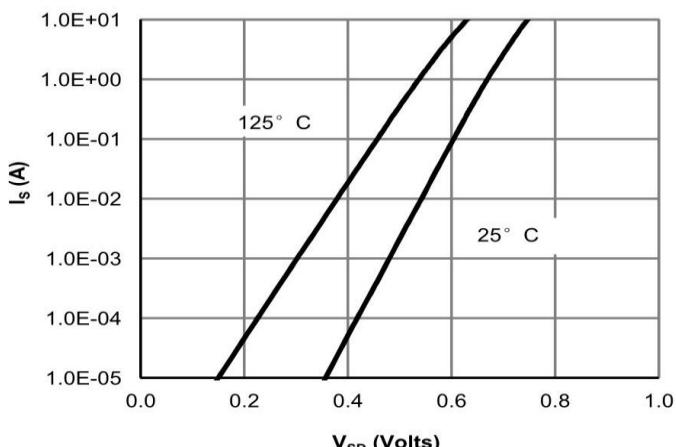
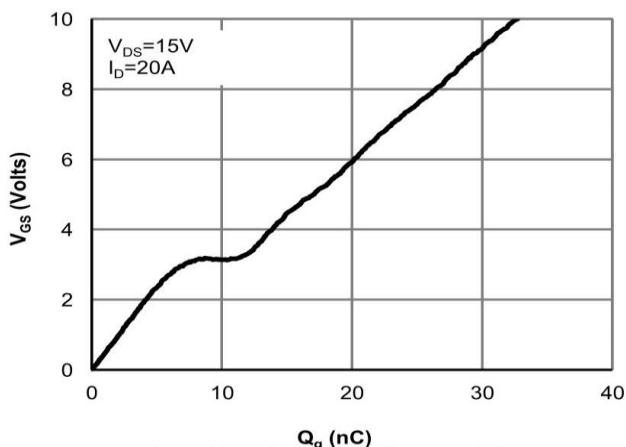
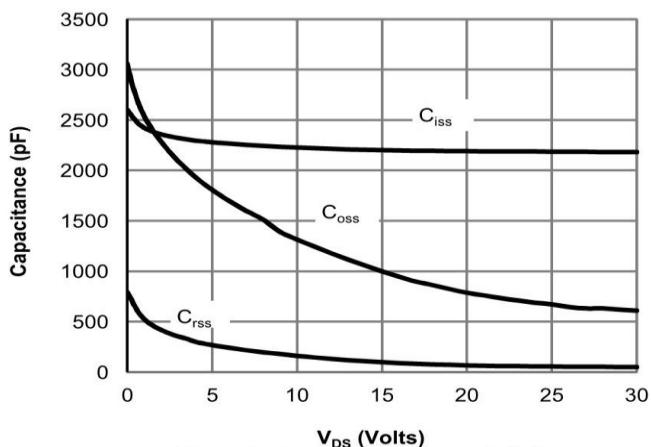
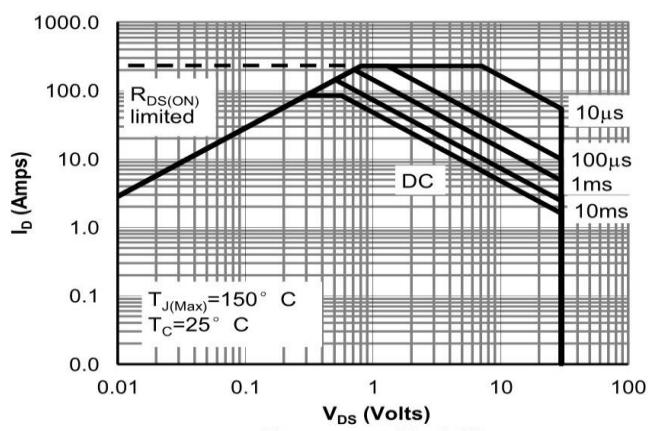
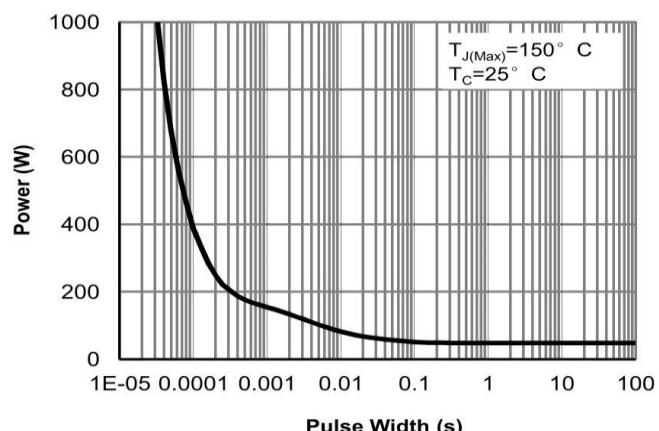
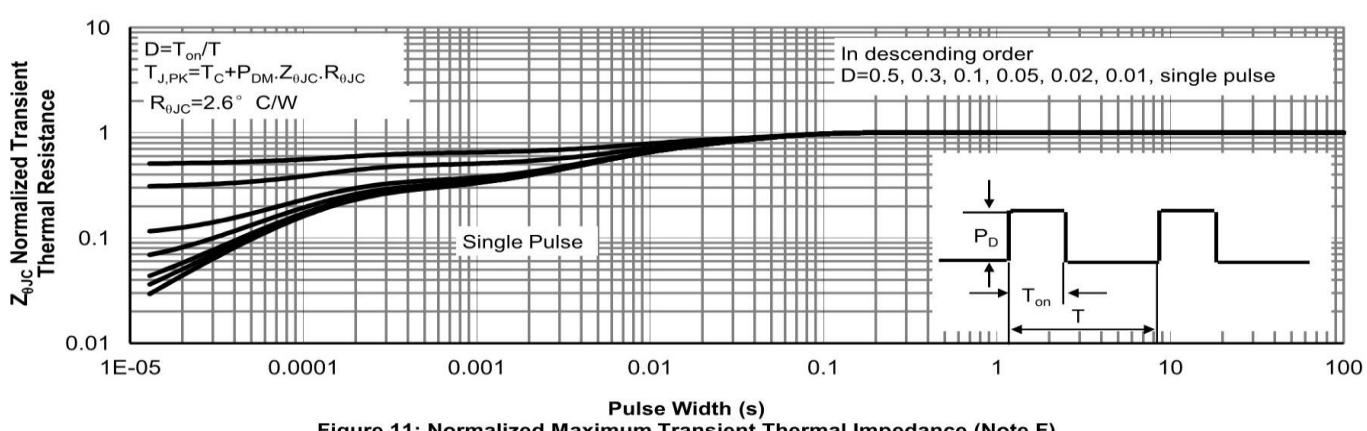


Figure 6: Body-Diode Characteristics (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

Figure 7: Gate-Charge Characteristics

Figure 8: Capacitance Characteristics

Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

Figure 10: Single Pulse Power Rating Junction-to-Case (Note F)

Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

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